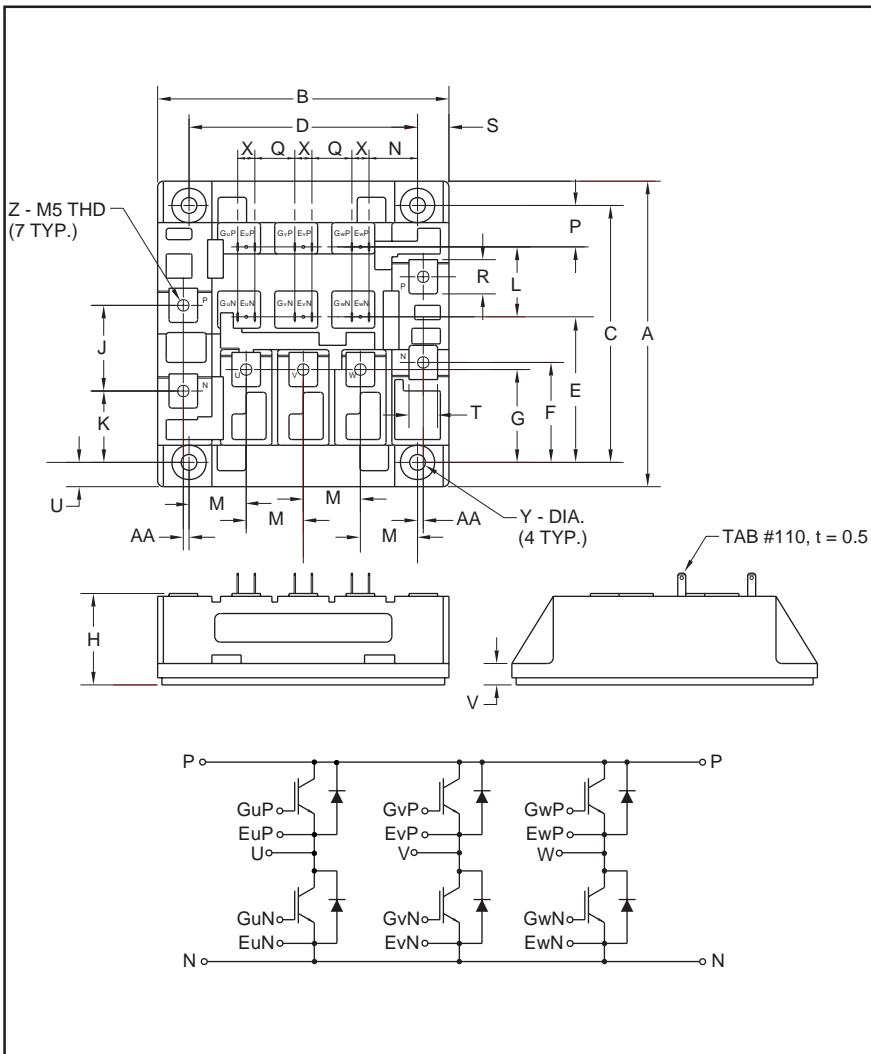


MITSUBISHI IGBT MODULES  
**CM75TF-24H**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE



**Description:**  
 Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

- Features:**
- Low Drive Power
  - Low  $V_{CE(sat)}$
  - Discrete Super-Fast Recovery Free-Wheel Diode
  - High Frequency Operation
  - Isolated Baseplate for Easy Heat Sinking

- Applications:**
- AC Motor Control
  - Motion/Servo Control
  - UPS
  - Welding Power Supplies

**Ordering Information:**  
 Example: Select the complete part module number you desire from the table below -i.e. CM75TF-24H is a 1200V ( $V_{CES}$ ), 75 Ampere Six-IGBT Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	75	24

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	4.02	102.0
C	3.543±0.01	90.0±0.25
D	3.15±0.01	80.0±0.25
E	2.01	51.0
F	1.38	35.0
G	1.28	32.5
H	1.26 Max.	32.0 Max
J	1.18	30.0
K	0.98	25.0
L	0.96	24.5
M	0.79	20.0
N	0.67	17.0

Dimensions	Inches	Millimeters
P	0.57	14.5
Q	0.55	14.0
R	0.47	12.0
S	0.43	11.0
T	0.39	10.0
U	0.33	8.5
V	0.30	7.5
X	0.24	6.0
Y	0.22	5.5
Z	M5 Metric	M5
AA	0.08	2.0

## CM75TF-24H

HIGH POWER SWITCHING USE  
INSULATED TYPEAbsolute Maximum Ratings,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

	Symbol	Ratings	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{GES}$	$\pm 20$	Volts
Collector Current ( $T_C = 25\text{ }^\circ\text{C}$ )	$I_C$	75	Amperes
Peak Collector Current	$I_{CM}$	150*	Amperes
Emitter Current** ( $T_C = 25\text{ }^\circ\text{C}$ )	$I_E$	75	Amperes
Peak Emitter Current**	$I_{EM}$	150*	Amperes
Maximum Collector Dissipation ( $T_C = 25\text{ }^\circ\text{C}$ , $T_j \leq 150\text{ }^\circ\text{C}$ )	$P_c$	600	Watts
Mounting Torque, M5 Main Terminal	-	1.47 ~ 1.96	N · m
Mounting Torque, M5 Mounting	-	1.47 ~ 1.96	N · m
Weight	-	830	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{iso}$	2500	Vrms

\*Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$	-	-	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}$ , $V_{CE} = 0V$	-	-	0.5	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 7.5\text{mA}$ , $V_{CE} = 10V$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 75A$ , $V_{GE} = 15V$	-	2.5	3.4**	Volts
		$I_C = 75A$ , $V_{GE} = 15V$ , $T_j = 150\text{ }^\circ\text{C}$	-	2.25	-	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 600V$ , $I_C = 75A$ , $V_{GE} = 15V$	-	375	-	nC
Emitter-Collector Voltage	$V_{EC}$	$I_E = 75A$ , $V_{GE} = 0V$	-	-	3.5	Vrms

\*\* Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		-	-	15	nF
Output Capacitance	$C_{oes}$	$V_{GE} = 0V$ , $V_{CE} = 10V$	-	-	5.3	nF
Reverse Transfer Capacitance	$C_{res}$		-	-	3	nF
Resistive	Turn-on Delay Time	$V_{CC} = 600V$ , $I_C = 75A$ , $V_{GE1} = V_{GE2} = 15V$ , $R_G = 4.2\Omega$	-	-	150	ns
	Load					
Switching	Turn-off Delay Time	$V_{CC} = 600V$ , $I_C = 75A$ , $V_{GE1} = V_{GE2} = 15V$ , $R_G = 4.2\Omega$	-	-	250	ns
	Time					
Diode Reverse Recovery Time	$t_{rr}$	$I_E = 75A$ , $di_E/dt = -150A/\mu\text{s}$	-	-	250	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_E = 75A$ , $di_E/dt = -150A/\mu\text{s}$	-	0.56	-	$\mu\text{C}$

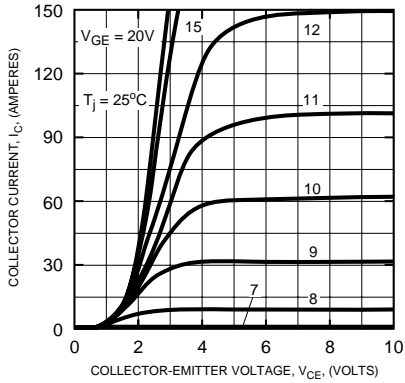
Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	-	-	0.21	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDi	-	-	0.47	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	-	-	0.025	$^\circ\text{C/W}$

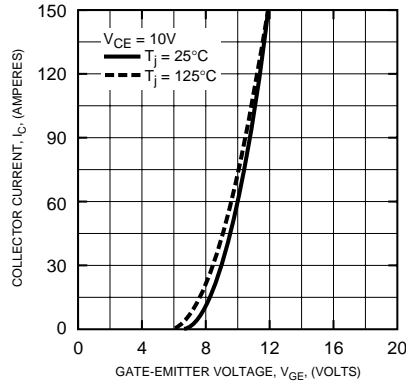
# CM75TF-24H

HIGH POWER SWITCHING USE  
INSULATED TYPE

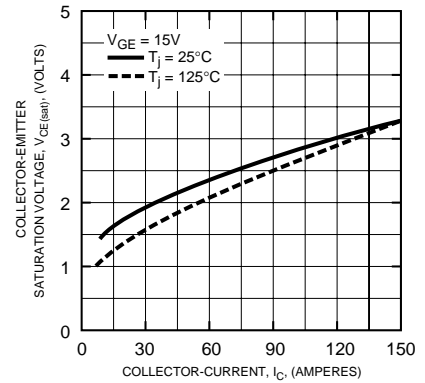
**OUTPUT CHARACTERISTICS (TYPICAL)**



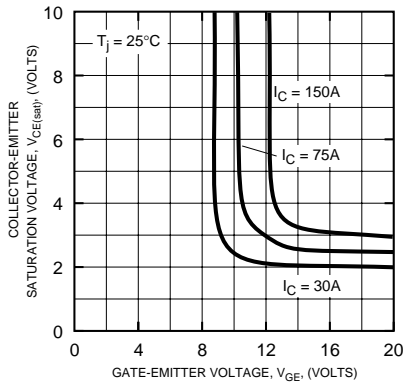
**TRANSFER CHARACTERISTICS (TYPICAL)**



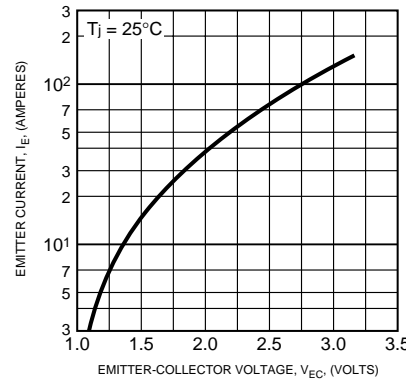
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



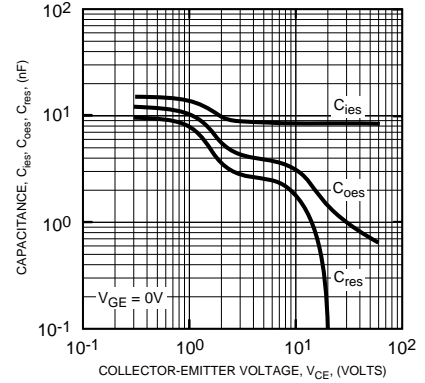
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



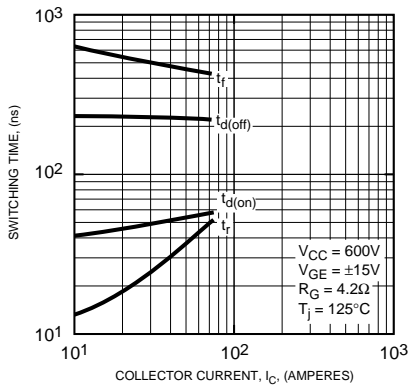
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



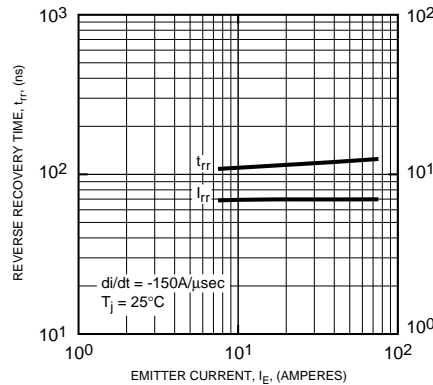
**CAPACITANCE VS.  $V_{CE}$  (TYPICAL)**



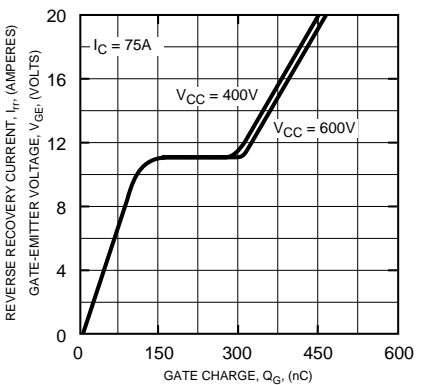
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**



**REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**



**GATE CHARGE,  $V_{GE}$**



# CM75TF-24H

HIGH POWER SWITCHING USE  
INSULATED TYPE

